

REMARKS

Claims 1-25 are pending in the present application. Claims 5-7, 14, 18-19, and 23-24 have been withdrawn.

Response to Election

With respect to the election of species III, the examiner argues that claims 8-13, 20 and 25 describe none of the species because the recitation "CMOS technology". Applicants argue that these claims are readable on species III (FIGS. 5 and 6). FIG. 5 shows two switching devices M1 and M2 formed on an integrated circuit 22. In FIG. 5, the switching device M2 is formed in a deep N-well. The Specification describes how this arrangement can be formed using CMOS technology. For example, the Specification recites:

"In recent generations of CMOS and other technologies, a "deep N-well", or "triple well", is available. Generally, when using a deep N-well, three wells are present: an N-well, a P-well, and a deep N-well. Deep N-wells were developed to help with RF isolation issues, but are used in the present invention to permit the integration of a stacked CMOS power amplifier." Specification, page 8, para. 20.

To help advance the present patent application, claims 8, 20, and 25 have been withdrawn. Claim 9 has been amended to delete "CMOS" in lines 2 and 3. This amendment to claim 9 was not made in response to any prior art rejections.

Drawings

The examiner has objected to the drawings for not showing CMOS technology. While Applicant asserts that this objection is not warranted, the objection is moot in view of the amendment to claim 9, and the withdrawal of claims 8, 20, and 25.

Claim Objections

Claim 21 has been amended to replace "first" with "second." This amendment to claim 21 was not made in response to any prior art rejections.

Claim Rejections

Claims 1-3, 15, 16, 21 and 22 have been rejected under § 102(b) as being anticipated by FIG. 4 of Sakurai.

Claim 1 recites an RF power amplifier including "a first power amplifier formed on the integrated circuit, the first power amplifier having a first switching device," "a second power amplifier formed on the integrated circuit, the second power amplifier having a second switching device, wherein the first and second power amplifiers are connected in a stacked arrangement between a voltage supply and ground," and "wherein the first and second switching devices are electrically isolated from each other."

FIG. 4 of Sakurai shows the structure of a clamping circuit implemented according the circuit diagram shown in FIG. 1. The circuit shown in FIG. 1 shows a clamping circuit having three N-MOS transistors connected in series with the gate of each transistor connected to its drain. The Examiner argues that the left and middle transistors shown in FIG. 4 of Sakurai are first and second amplifiers connected in a stacked arrangement between a voltage supply and ground. Applicant asserts that Sakurai does not teach or suggest an RF power amplifier having first and second amplifiers configured in a stacked arrangement. The circuits described in Sakurai are not RF power amplifiers, but are clamping circuits, whose purpose is keep a node (A) at a desired voltage level.

For at least these reasons, applicant asserts that claim 1 is allowable over the prior art. Since dependent claims 2-3 depend from claim 1, it is also believed that these claims are allowable over the prior art.

Although claim 9 was not rejected based on the prior art (since the Examiner considered claims 9-13 as non-elected claims), claim 9 will be discussed with respect to the Sakurai reference.

Amended claim 9 recites a method of making a stacked RF power amplifier including "forming first and second stacked power amplifiers on the integrated circuit, wherein the first and second stacked power amplifiers each include at least one switching device" and "electrically isolating a switching device of the first power amplifier with a switching device of the second power amplifier." Applicant asserts that Sakurai does not teach or suggest making a stacked RF power amplifier by forming first and second stacked power amplifiers in an integrated circuit.

For at least these reasons, and for the reasons set forth with respect to claim 1, applicant asserts that amended claim 9 is allowable over the prior art. Since dependent claims 10-13 depend from amended claim 9, it is also believed that these claims are allowable over the prior art.

Claim 15 recites a stacked RF power amplifier including "first and second stacked power amplifiers, wherein each power amplifier includes at least one switching device having a substrate" and "wherein the body of a switching device in the first power amplifier is electrically isolated from the body of a switching device in the second power amplifier." Applicant asserts that Sakurai does not teach or suggest the invention recited in claim 15. For at least these reasons, and reasons set forth above, applicant asserts that claim 15 is allowable over the prior art. Since dependent claim 16 depends from claim 15, it is also believed that claim 16 is allowable over the prior art.

Claim amended 21 recites a stacked RF power amplifier formed on an integrated circuit including "a first transistor formed on the integrated circuit, the first transistor having a transistor

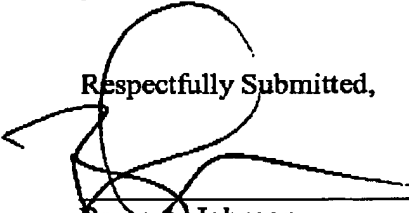
body," "a second transistor formed on the integrated circuit, the second transistor having a transistor body," and "wherein the transistor body of the first transistor is isolated from the transistor body of the second transistor." Applicant asserts that Sakurai does not teach or suggest the invention recited in amended claim 21. For at least these reasons, and reasons set forth above, applicant asserts that amended claim 21 is allowable over the prior art. Since dependent claim 22 depends from claim 21, it is also believed that claim 22 is allowable over the prior art.

Conclusion

It is respectfully submitted that all claims are patentable over the prior art. It is further more respectfully submitted that all other matters have been addressed and remedied and that the application is in form for allowance. Should there remain unresolved issues that require adverse action, it is respectfully requested that the Examiner telephone Bruce A. Johnson, Applicants' Attorney at 512-301-9900 so that such issues may be resolved as expeditiously as possible.

10-14-05
Date

Respectfully Submitted,



Bruce A. Johnson
Reg. No. 37361
Attorney for Applicant(s)

Customer Number 30163
Bruce A. Johnson
Johnson & Associates
PO Box 90698
Austin, TX 78709-0698
Tel. 512-301-9900
Fax 512-301-9915